Vladimir Aleshkin

List of Publications by Citations

178 papers	1,086 citations	16 h-index	27 g-index
195 ext. papers	1,315 ext. citations	1.2 avg, IF	4.01 L-index

#	Paper	IF	Citations
178	Terahertz surface plasmons in optically pumped graphene structures. *Journal of Physics Condensed Matter*, **2011**, 23, 145302	1.8	127
177	Feasibility of terahertz lasing in optically pumped epitaxial multiple graphene layer structures. *Journal of Applied Physics*, **2009**, 106, 084507	2.5	109
176	Cyclotron resonance and interband optical transitions in HgTe/CdTe(0 1 3) quantum well heterostructures. *Semiconductor Science and Technology*, **2011**, 26, 125011	1.8	37
175	Injection terahertz laser using the resonant inter-layer radiative transitions in double-graphene-layer structure. *Applied Physics Letters*, **2013**, 103, 163507	3.4	34
174	Terahertz laser based on optically pumped graphene: Model and feasibility of realization. *JETP Letters*, **2009**, 89, 63-67	1.2	31
173	Exchange enhancement of the g factor in InAs/AlSb heterostructures. *Semiconductors*, **2008**, 42, 828-833	0.7	31
172	Study of lifetimes and photoconductivity relaxation in heterostructures with Hg x Cd1 □x Te/Cd y Hg1 □y Te quantum wells. *Semiconductors*, **2012**, 46, 1362-1366	0.7	27
171	Self-organization of germanium nanoislands obtained in silicon by molecular-beam epitaxy. *JETP Letters*, **1998**, 67, 48-53	1.2	27
170	Voltage-tunable terahertz and infrared photodetectors based on double-graphene-layer structures. *Applied Physics Letters*, **2014**, 104, 163505	3.4	25
169	Terahertz spectroscopy of quantum-well narrow-bandgap HgTe/CdTe-based heterostructures. *JETP Letters*, **2010**, 92, 756-761	1.2	24
168	Valence band energy spectrum of HgTe quantum wells with an inverted band structure. *Physical Review B*, **2017**, 96,	3.3	22
167	Graphene vertical cascade interband terahertz and infrared photodetectors. *2D Materials*, **2015**, 2, 025002	7.9	19
166	Shallow acceptors in strained Ge/Ge1□ Six heterostructures with quantum wells. *Semiconductors*, **2000**, 34, 563-567	0.7	19
165	Monolithically integrated InGaAs/GaAs/AlGaAs quantum well laser grown by MOCVD on exact Ge/Si(001) substrate. *Applied Physics Letters*, **2016**, 109, 061111	3.4	19
164	Room-temperature intracavity difference-frequency generation in butt-joint diode lasers. *Applied Physics Letters*, **2008**, 92, 021122	3.4	17
163	Difference mode generation in injection lasers. *Semiconductors*, **2001**, 35, 1203-1207	0.7	16
162	Spectra of persistent photoconductivity in InAs/AlSb quantum-well heterostructures. *Semiconductors*, **2005**, 39, 22	0.7	15

161	Cyclotron resonance in doped and undoped InAs/AlSb heterostructures with quantum wells. *Semiconductors*, **2005**, 39, 62	0.7	15
160	Surface-plasmons lasing in double-graphene-layer structures. *Journal of Applied Physics*, **2014**, 115, 04451[illegible]	1.5	14
159	High-field splitting of the cyclotron resonance absorption in strained p-InGaAs/GaAs quantum wells. *Physical Review B*, **2009**, 79,	3.3	14
158	Nonlinear mode mixing in dual-wavelength semiconductor lasers with tunnel junctions. *Applied Physics Letters*, **2007**, 90, 171106	3.4	13
157	Fundamental Limits to Far-Infrared Lasing in Auger-Suppressed HgCdTe Quantum Wells. *ACS Photonics*, **2020**, 7, 98-104	6.3	13
156	Negative terahertz conductivity and amplification of surface plasmons in graphene[illegible]black phosphorus injection laser heterostructures. *Physical Review B*, **2019**, 100,	3.3	12
155	Impurity resonance states in semiconductors. *Semiconductors*, **2008**, 42, 880-904	0.7	12
154	Direct band Ge and Ge/InGaAs quantum wells in GaAs. *Journal of Applied Physics*, **2011**, 109, 123107	2.5	11
153	Non-linear wave mixing in GaAs/InGaAs/InGaP butt-joint diode lasers. *Journal of Modern Optics*, **2005**, 52, 2323-2330	1.1	11
152	Carrier Recombination, Long-Wavelength Photoluminescence, and Stimulated Emission in HgCdTe Quantum Well Heterostructures. *Physica Status Solidi (B): Basic Research*, **2019**, 256, 1800546	1.3	10
151	Interband infrared photodetectors based on HgTe[illegible]CdHgTe quantum-well heterostructures. *Optical Materials Express*, **2018**, 8, 1349	2.6	10
150	Landau level spectroscopy of valence bands in HgTe quantum wells: effects of symmetry lowering. *Journal of Physics Condensed Matter*, **2019**, 31, 145501	1.8	10
149	Radiative recombination in narrow gap HgTe/CdHgTe quantum well heterostructures for laser applications. *Journal of Physics Condensed Matter*, **2018**, 30, 495301	1.8	10
148	MOCVD Growth of InGaAs/GaAs/AlGaAs Laser Structures with Quantum Wells on Ge/Si Substrates. *Crystals*, **2018**, 8, 311	2.3	9
147	Mode structure in the far field radiation of a leaky-wave multiple quantum well laser. *Quantum Electronics*, **2012**, 42, 931-933	1.8	9
146	Terahertz emission and photoconductivity in n-type GaAs/AlGaAs quantum wells: the role of resonant impurity states. *Semiconductors*, **2010**, 44, 1394-1397	0.7	9
145	HgCdTe-based quantum cascade lasers operating in the GaAs phonon Reststrahlen band predicted by the balance equation method. *Optics Express*, **2020**, 28, 25371-25382	3.3	9
144	Magnetospectroscopy of double HgTe/CdHgTe quantum wells. *Semiconductors*, **2016**, 50, 1532-1538	0.7	8

143	Tunable source of terahertz radiation based on the difference-frequency generation in a GaP crystal. *JETP Letters*, **2008**, 88, 787-789	1.2	8
142	Fano resonance study in impurity photocurrent spectra of bulk GaAs and GaAs quantum wells doped with shallow donors. *Physical Review B*, **2007**, 75,	3.3	8
141	Temperature limitations for stimulated emission in 3 h range due to threshold and non-threshold Auger recombination in HgTe/CdHgTe quantum wells. *Applied Physics Letters*, **2020**, 117, 083103	3.4	8
140	Electron and hole spectra and selection rules for optical transitions in Ge1 Six/Ge heterostructures. *Semiconductors*, **1997**, 31, 132-138	0.7	7
139	Photoelectric properties of GaAs/InAs heterostructures with quantum dots. *Semiconductors*, **1997**, 31, 941-946	0.7	7
138	Giant population inversion of hot electrons in GaAs/AlAs type heterostructures with quantum wells. *JETP Letters*, **1998**, 68, 78-83	1.2	7
137	Terahertz oscillator based on nonlinear frequency conversion in a double vertical cavity. *Semiconductors*, **2005**, 39, 113	0.7	7
136	1.3 h photoluminescence of Ge/GaAs multi-quantum-well structure. *Journal of Applied Physics*, **2014**, 115, 043512	2.5	6
135	Waveguide effect of GaAsSb quantum wells in a laser structure based on GaAs. *Semiconductors*, **2013**, 47, 1475-1477	0.7	6
134	Determination of the density of states in quantum wells and quantum dot arrays by the capacitance-voltage method. *Semiconductors*, **1999**, 33, 1133-1138	0.7	6
133	On the stimulated emission of InGaAs/GaAs/AlGaAs laser structures grown by MOCVD on exact and inclined Ge/Si(001) substrates. *Semiconductors*, **2017**, 51, 663-666	0.7	5
132	Guiding effect of quantum wells in semiconductor lasers. *Quantum Electronics*, **2013**, 43, 401-406	1.8	5
131	On the band spectrum in p-type HgTe/CdHgTe heterostructures and its transformation under temperature variation. *Semiconductors*, **2017**, 51, 1531-1536	0.7	5
130	Peculiarities of growing InGaAs/GaAs/AlGaAs laser structures by MOCVD on Ge/Si substrates. *Semiconductors*, **2017**, 51, 1527-1530	0.7	5
129	Efficiency of GaInAs/GaAs quantum-well lasers upon inhomogeneous excitation of quantum wells. *Quantum Electronics*, **2013**, 43, 999-1002	1.8	5
128	Nonlinear frequency conversion in a double vertical-cavity surface-emitting laser. *Semiconductors*, **2004**, 38, 1350-1355	0.7	5
127	The mode competition, instability, and second harmonic generation in dual-frequency InGaAs/GaAs/InGaP lasers. *Semiconductors*, **2005**, 39, 156	0.7	5
126	Resonant states of shallow acceptors in uniaxially deformed germanium. *Journal of Experimental and Theoretical Physics*, **2001**, 93, 1296-1301	1	5

125	Infrared radiation from hot holes during spatial transport in selectively doped InGaAs/GaAs heterostructures with quantum wells. *JETP Letters*, **1996**, 64, 520-524	1.2	5
124	Study of the Auger Recombination Energy Threshold in a Series of Waveguide Heterostructures with HgTe/Cd0.7Hg0.3Te QWs Near 14 Ēh. *Semiconductors*, **2019**, 53, 1154-1157	0.7	4
123	Picosecond photoluminescence dynamics in an InGaAs/GaAs quantum-well heterostructure. *Semiconductors*, **2012**, 46, 917-920	0.7	4
122	Technology of the production of laser diodes based on GaAs/InGaAs/AlGaAs structures grown on a Ge/Si substrate. *Semiconductors*, **2017**, 51, 1477-1480	0.7	4
121	Stimulated emission from an InGaAs/GaAs/AlGaAs heterostructure grown on a Si substrate. *JETP Letters*, **2015**, 100, 795-797	1.2	4
120	Leaky-wave semiconductor laser with improved energetic characteristics and very narrow dirrectional pattern. *Quantum Electronics*, **2010**, 40, 855-857	1.8	4
119	Intracavity terahertz difference-frequency generation in an InGaAs-quantum-well two-frequency InGaAsP/InP laser. *Quantum Electronics*, **2009**, 39, 727-730	1.8	4
118	Difference-frequency generation in a butt-join diode laser. *Semiconductors*, **2009**, 43, 208-211	0.7	4
117	A multifrequency interband two-cascade laser. *Semiconductors*, **2007**, 41, 1209-1213	0.7	4
116	Inversion of the electron population in subbands of dimensional quantization with longitudinal transport in tunnel-coupled quantum wells. *Semiconductors*, **2002**, 36, 685-690	0.7	4
115	On the impurity photoconductivity of uniaxially stressed p-Ge. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2003**, 680-682		4
114	Threshold energies of Auger recombination in HgTe/CdHgTe quantum well heterostructures with 30-70 meV bandgap. *Journal of Physics Condensed Matter*, **2019**, 31, 425301	1.8	4
113	Auger recombination in narrow gap HgCdTe/CdHgTe quantum well heterostructures. *Journal of Applied Physics*, **2021**, 129, 133106	2.5	4
112	Effect of Features of the Band Spectrum on the Characteristics of Stimulated Emission in Narrow-Gap Heterostructures with HgCdTe Quantum Wells. *Semiconductors*, **2018**, 52, 1375-1379	0.7	4
111	Submonolayer InGaAs/GaAs Quantum Dots Grown by MOCVD. *Semiconductors*, **2019**, 53, 1138-1142	0.7	3
110	Observation of dynamics of impurity photoconductivity in n-GaAs caused by electron cooling. *Semiconductors*, **2015**, 49, 113-117	0.7	3
109	Dynamics of the cascade capture of electrons by charged donors in GaAs and InP. *Journal of Experimental and Theoretical Physics*, **2016**, 123, 284-291	1	3
108	Lowering the Lasing Threshold by Doping in Mid-Infrared Lasers Based on HgCdTe with HgTe Quantum Wells. *Semiconductors*, **2018**, 52, 1221-1224	0.7	3

107	Efficiency of vertical emission from a semiconductor laser waveguide with a diffraction grating. *Semiconductors*, **2014**, 48, 89-94	0.7	3
106	Structural and optical properties of GaAs-based heterostructures with Ge and Ge/InGaAs quantum wells. *Semiconductors*, **2013**, 47, 636-640	0.7	3
105	Dependence of the ground-state transition energy versus optical pumping in GaAsSb/InGaAs/GaAs heterostructures. *Applied Physics Letters*, **2014**, 104, 021108	3.4	3
104	Simultaneous TE1 and TE2 mode lasing yielding dual-wavelength oscillation in a semiconductor laser with a tunnel junction. *Semiconductors*, **2011**, 45, 641-645	0.7	3
103	Anomalous characteristics of lasers with a large number of quantum wells. *Technical Physics*, **2011**, 56, 1049-1052	0.5	3
102	Fano resonances in the impurity photocurrent spectra of GaAs samples and an InGaAs/GaAsP quantum-well heterostructure doped with shallow acceptors. *Journal of Experimental and Theoretical Physics*, **2009**, 109, 466-471	1	3
101	Far Infrared Emission and Absorption (Amplification) under Real Space Transfer and Population Inversion in Shallow Multi-Quantum-Wells. *Physica Status Solidi (B): Basic Research*, **1997**, 204, 563-565	1.3	3
100	Monte Carlo simulation of 2D TASER. *Journal of Computational Electronics*, **2007**, 6, 45-48	1.8	3
99	Fano resonance in the impurity photoconductivity spectrum of InP doped with shallow donors. *Physics of the Solid State*, **2008**, 50, 1211-1214	0.8	3
98	Fano resonances in the impurity photoexcitation spectra of semiconductors doped with shallow donors. *Journal of Experimental and Theoretical Physics*, **2005**, 101, 708-716	1	3
97	The use of a scanning tunneling microscope (STM) for investigation of local photoconductivity of quantum-dimensional semiconductor structures. *Technical Physics Letters*, **2000**, 26, 1-3	0.7	3
96	Plasmon recombination in narrowgap HgTe quantum wells. *Journal of Physics Communications*, **2020**, 4, 115012	1.2	3
95	Stimulated emission in heterostructures with double InGaAs/GaAsSb/GaAs quantum wells, grown on GaAs and Ge/Si(001) substrates. *Semiconductors*, **2016**, 50, 1435-1438	0.7	3
94	On the Application of Strain-Compensating GaAsP Layers for the Growth of InGaAs/GaAs Quantum-Well Laser Heterostructures Emitting at Wavelengths above 1100 nm on Artificial Ge/Si Substrates. *Semiconductors*, **2018**, 52, 1547-1550	0.7	3
93	Effect of Cd content in barriers on the threshold energy of Auger recombination in waveguide structures with HgTe/CdxHg1-xTe quantum wells, emitting at a wavelength of 18 μm. *Quantum Electronics*, **2019**, 49, 556-558	1.8	2
92	Spin-orbit splitting of the conduction band in HgTe quantum wells: Role of different mechanisms. *Physica E: Low-Dimensional Systems and Nanostructures*, **2019**, 110, 95-99	3	2
91	Terahertz Emission from HgCdTe QWs under Long-Wavelength Optical Pumping. *Journal of Infrared, Millimeter, and Terahertz Waves*, **2020**, 41, 750-757	2.2	2
90	Experimental determination of the optimum number of quantum wells in multiwell heterolasers with radiation leakage into a substrate. *Technical Physics Letters*, **2014**, 40, 432-434	0.7	2

89	The waveguide effect of InGaAs quantum wells in a GaAs structure on Si substrate with Ge buffer layer. *Technical Physics Letters*, **2015**, 41, 648-650	0.7	2
88	Calculation of the parameters for the Fano resonance in the impurity photocurrent spectrum of semiconductors doped with hydrogen-like donors. *Semiconductor Science and Technology*, **2010**, 25, 085005	1.8	2
87	Deep states in silicon □doped GaAs. *Semiconductors*, **1998**, 32, 659-664	0.7	2
86	Generation of difference-frequency radiation in mid- and far-IR ranges by using subpicosecond and picosecond semiconductor lasers. *Quantum Electronics*, **2008**, 38, 149-153	1.8	2
85	Picosecond kinetics of photoexcited carriers in gallium arsenide containing aluminum nanoclusters. *Semiconductors*, **2007**, 41, 909-913	0.7	2
84	Oscillations at a difference frequency in the middle and far infrareds in GaP semiconductor waveguides. *Technical Physics*, **2006**, 51, 1207-1209	0.5	2
83	Shallow-impurity-assisted transitions in the course of submillimeter magnetoabsorption of strained Ge/GeSi(111) quantum-well heterostructures. *Physics of the Solid State*, **2004**, 46, 125-129	0.8	2
82	Intersubband cyclotron resonance of holes in strained Ge/GeSi(111) heterostructures with germanium wide quantum wells and cyclotron resonance of 1L electrons in GeSi layers. *Physics of the Solid State*, **2004**, 46, 130-137	0.8	2
81	Blue-green radiation in GaAs-based quantum-well lasers. *Semiconductors*, **2004**, 38, 352-354	0.7	2
80	Mid-IR stimulated emission in Hg(Cd)Te/CdHgTe quantum well structures up to 200 K due to suppressed Auger recombination. *Laser Physics*, **2021**, 31, 015801	1.2	2
79	Investigation into Microwave Absorption in Semiconductors for Frequency-Multiplication Devices and Radiation-Output Control of Continuous and Pulsed Gyrotrons. *Semiconductors*, **2020**, 54, 1069-1074	0.7	2
78	Polarization-Sensitive Fourier-Transform Spectroscopy of HgTe/CdHgTe Quantum Wells in the Far Infrared Range in a Magnetic Field. *JETP Letters*, **2018**, 108, 329-334	1.2	2
77	Magnetoabsorption in HgCdTe/CdHgTe Quantum Wells in Tilted Magnetic Fields. *JETP Letters*, **2019**, 109, 191-197	1.2	1
76	Nonlinear harmonic mixing in an InGaAs/InGaP/GaAs laser on a germanium substrate. *Quantum Electronics*, **2015**, 45, 204-206	1.8	1
75	Temporal dynamics of impurity photoconductivity in n-GaAs and n-InP. *Physics of the Solid State*, **2014**, 56, 917-921	0.8	1
74	Nonresonant radiative exciton transfer by near field between quantum wells. *Journal of Experimental and Theoretical Physics*, **2013**, 117, 944-949	1	1
73	Shot noise suppression and coherent tunneling in a triple barrier resonant diode **2013**,		1
72	On the cascade capture of electrons at charged dipoles in weakly compensated semiconductors. *Semiconductors*, **2017**, 51, 1444-1448	0.7	1

71	Dual-frequency GaAs/InGaP laser diode with a GaAsSb quantum well. *Semiconductors*, **2017**, 51, 1360-1363	0.7	1
70	The temporal dynamics of impurity photoconductivity in quantum wells in GaAs. *Journal of Experimental and Theoretical Physics*, **2015**, 121, 647-652	1	1
69	On a semiconductor laser with a p□ tunnel junction with radiation emission through the substrate. *Semiconductors*, **2015**, 49, 1440-1442	0.7	1
68	Optimization of InGaP/GaAs/InGaAs heterolasers with tunnel-coupled waveguides. *Semiconductors*, **2015**, 49, 1571-1574	0.7	1
67	Substrate-emitting semiconductor laser with a trapezoidal active region. *Quantum Electronics*, **2014**, 44, 286-288	1.8	1
66	Long-wavelength shift and enhanced room temperature photoluminescence efficiency in GaAsSb/InGaAs/GaAs-based heterostructures emitting in the spectral range of 1.0□1.2 □m due to increased charge carrier□ localization. *Journal of Applied Physics*, **2014**, 116, 203102	2.5	1
65	Near-field mechanism of photoluminescence excitation in quantum well heterostructures. *JETP Letters*, **2012**, 94, 811-815	1.2	1
64	Cyclotron resonance in HgCdTe-based heterostructures in strong magnetic fields. *Journal of Physics: Conference Series*, **2013**, 461, 012038	0.3	1
63	Resonance Coulomb scattering by shallow donor impurities in GaAs and InP. *Semiconductor Science and Technology*, **2011**, 26, 095003	1.8	1
62	Theory of the Fano resonance in impurity excitation spectra of p-GaAs. *Physics of the Solid State*, **2011**, 53, 1176-1185	0.8	1
61	Polarization of in-plane photoluminescence from InAs/Ga(In)As quantum-well layers grown by metallorganic vapor-phase epitaxy. *Semiconductors*, **1998**, 32, 1119-1124	0.7	1
60	Shallow acceptors in strained multiquantum-well Ge/Ge1□ Six heterostructures. *Semiconductors*, **1998**, 32, 1106-1110	0.7	1
59	GaAsSb/GaAs quantum well growth by MOCVD hydride epitaxy with laser sputtering of antimony. *JETP Letters*, **1998**, 68, 91-96	1.2	1
58	Generation of difference-frequency radiation in the far- and mid-IR ranges in a two-chip laser based on gallium arsenide on a germanium substrate. *Quantum Electronics*, **2008**, 38, 855-858	1.8	1
57	Experimental study of nonlinear mode mixing in dual-wavelength semiconductor lasers. *Laser Physics*, **2007**, 17, 684-687	1.2	1
56	Difference-frequency pulse generation in quantum well heterolasers. *Laser Physics*, **2007**, 17, 688-694	1.2	1
55	Frequency shift in a system of two laser diodes. *Semiconductors*, **2007**, 41, 1364-1368	0.7	1
54	Optical band gap width in GaAs in megagauss magnetic fields. *Physics of the Solid State*, **2007**, 49, 634-645	0.8	1

53	Terahertz oscillator with vertical radiation extraction. *Technical Physics*, **2004**, 49, 592-597	0.5	1
52	Nonlinear mid-IR radiation in two-frequency semiconductor lasers with a corrugated waveguide. *Technical Physics*, **2004**, 49, 1486-1490	0.5	1
51	Population inversion between □ubbands in quantum wells under the conditions of □L intervalley transfer. *Semiconductors*, **2003**, 37, 215-219	0.7	1
50	Calculation of the states of shallow donors in quantum wells in a magnetic field using plane wave expansion. *Semiconductors*, **2005**, 39, 54	0.7	1
49	Negative photoconductivity of selectively doped SiGe/Si: B heterostructures with a two-dimensional hole gas in the middle-infrared range. *Physics of the Solid State*, **2005**, 47, 46	0.8	1
48	Toward Peltier-cooled mid-infrared HgCdTe lasers: Analyzing the temperature quenching of stimulated emission at ~6 □m wavelength from HgCdTe quantum wells. *Journal of Applied Physics*, **2021**, 130, 214302	2.5	1
47	Anisotropy of the in-plane g-factor of electrons in HgTe quantum wells. *Physical Review B*, **2020**, 101,	3.3	1
46	Continuous-Wave Stimulated Emission in the 10□14-□m Range under Optical Excitation in HgCdTe/CdHgTe-QW Structures with Quasirelativistic Dispersion. *Semiconductors*, **2020**, 54, 1371-1375	0.7	1
45	Express Characterization of the HgCdTe/CdHgTe Quantum Well Waveguide Heterostructures with the Quasi-Relativistic Carrier Dispersion Law by Room-Temperature Photoluminescence Spectroscopy. *Technical Physics Letters*, **2021**, 47, 154-157	0.7	1
44	Effect of antimony doping on the energy of optical transitions in n-Ge layers grown on Si (001) and Ge (001) substrates. *Journal of Applied Physics*, **2020**, 127, 165701	2.5	0
43	Efficient generation of the first waveguide mode in the InGaAs/GaAs/InGaP heterolaser. *Semiconductors*, **2008**, 42, 354-357	0.7	0
42	Impurity absorption of light involving resonant states of shallow donors in quantum wells. *Journal of Experimental and Theoretical Physics*, **2004**, 98, 1174-1182	1	0
41	Effects of the Electron□Electron Interaction in the Magneto-Absorption Spectra of HgTe/CdHgTe Quantum Wells with an Inverted Band Structure. *JETP Letters*, **2020**, 112, 508-512	1.2	0
40	Anomalous electron polarizability of HgTe quantum wells. *Physica E: Low-Dimensional Systems and Nanostructures*, **2021**, 128, 114606	3	0
39	Magnetooptics of HgTe/CdTe Quantum Wells with Giant Rashba Splitting in Magnetic Fields up to 34 T. *Semiconductors*, **2018**, 52, 1386-1391	0.7	0
38	Terahertz plasmons in doped HgTe quantum well heterostructures: dispersion, losses, and amplification. *Applied Optics*, **2021**, 60, 8991-8998	1.7	0
37	An observation of direct-gap electroluminescence in GaAs structures with Ge quantum wells. *Semiconductors*, **2015**, 49, 170-173	0.7	
36	Optical characteristics of laser diodes based on A3B5 compounds grown on germanium substrates. *Technical Physics Letters*, **2015**, 41, 304-306	0.7	

35	Variation of the emission frequency of a terahertz quantum cascade laser. *Technical Physics Letters*, **2016**, 42, 230-233	0.7
34	The exciton excitations and relaxation processes in low-dimensional semiconductor heterostructures with quantum wells. *Semiconductors*, **2016**, 50, 1691-1695	0.7
33	Method for narrowing the directional pattern of an InGaAs/GaAs/AlGaAs multiwell heterolaser. *Semiconductors*, **2016**, 50, 1488-1492	0.7
32	Stimulated emission from a metamorphic GaAsSb bulk layer on a GaAs substrate. *Semiconductors*, **2016**, 50, 586-589	0.7
31	Magnetooptical Studies and Stimulated Emission in Narrow Gap HgTe/CdHgTe Structures in the Very Long Wavelength Infrared Range. *Semiconductors*, **2018**, 52, 436-441	0.7
30	Near-field effect in the absorption spectrum of impurities in crystals. *JETP Letters*, **2014**, 99, 712-714	1.2
29	Investigation of GaAs/AlGaAs quantum cascade structures by optical methods based on hot luminescence in the near-infrared range. *Semiconductors*, **2014**, 48, 1463-1466	0.7
28	Spectral-kinetic properties of heterostructures with GaAsSb/InGaAs/GaAs-based quantum wells emitting in the range of 1.0–1.2 μm. *Semiconductors*, **2013**, 47, 1504-1507	0.7
27	Resonance Coulomb scattering at shallow donors in AlGaAs/n-GaAs/AlGaAs quantum wells. *Semiconductors*, **2013**, 47, 487-493	0.7
26	Activation conductivity in HgTe/CdHgTe quantum wells at integer Landau level filling factors: Role of the random potential. *Semiconductors*, **2017**, 51, 1562-1570	0.7
25	On the cascade capture of electrons at donors in GaAs quantum wells. *Semiconductors*, **2015**, 49, 1197-1201	0.7
24	Features in the impurity photoconductivity spectra ofn-GaAs andn-InP at energies multiple of the optical phonon energy. *Semiconductor Science and Technology*, **2012**, 27, 115008	1.8
23	Optical detection of an electric field in a GaAs/AlGaAs n-i-n heterostructure with double quantum wells. *JETP Letters*, **2011**, 93, 394-398	1.2
22	Polarization dependence of Fano resonances in impurity photoconductivity of quantum wells doped with shallow donors. *Physics of the Solid State*, **2011**, 53, 1253-1262	0.8
21	Simultaneous generation of TE 0 and TE 1 modes with different wavelengths in a semiconducting laser diode. *Technical Physics*, **2009**, 54, 1711-1713	0.5
20	Calculation of the parameters for the Fano resonance in the impurity photocurrent spectrum of semiconductors doped with hydrogen-like donors. *Semiconductor Science and Technology*, **2011**, 26, 049501	1.8
19	Characterization of GaAs/ InxGa1−x As quantum-dot heterostructures by electrical and optical methods. *Semiconductors*, **1998**, 32, 99-104	0.7
18	Impurity photoconductivity in strained p-InGaAs/GaAsP heterostructures. *JETP Letters*, **2008**, 88, 197-200	1.2

17	Study of interband cascade lasers with tunneling transition. *Bulletin of the Russian Academy of Sciences: Physics*, **2007**, 71, 96-99	0.4
16	Generation of self-sustained pulsations of radiation in InGaAs/GaAs/InGaP quantum-well lasers. *Journal of Applied Spectroscopy*, **2007**, 74, 589-593	0.7
15	THE MONTE-CARLO SIMULATION OF TRANSPORT IN QUANTUM WELL GaAs/AlGaAs HETEROSTRUCTURE DOPED WITH SHALLOW DONORS UNDER IMPURITY BREAKDOWN. *International Journal of Nanoscience*, **2007**, 06, 253-256	0.6
14	Parametric optimization of the Bragg reflectors in a laser with the vertical cavity and nonlinear frequency conversion. *Semiconductors*, **2006**, 40, 486-490	0.7
13	Analysis of gain and loss anisotropy in the guiding structure of a long-wave intervalley-transfer laser. *Technical Physics*, **2002**, 47, 788-791	0.5
12	Observation of the middle-infrared emission from semiconductor lasers generating two frequency lines in the near-infrared region of the spectrum. *Semiconductors*, **2005**, 39, 139	0.7
11	Shallow acceptor levels in Ge/GeSi heterostructures with quantum wells in a magnetic field. *Physics of the Solid State*, **2005**, 47, 76	0.8
10	Zero-phonon and dipole □X electron transitions in GaAs/AlAs quantum-well heterostructures in a longitudinal electric field. *Semiconductors*, **2000**, 34, 575-582	0.7
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